



# Burn-in & Test Socket Workshop

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# Technical Program

Session 1

Monday 3/05/01 8:30AM

## Burn-in: Product Trends And Manufacturing Challenges

**“Facing The Power Of The Future - High End Burn-in Directions And Trends”**

Marc Knox - IBM Microelectronics

**“Burn-in Of Memory Devices - A Look At The Past, Present And Future Of  
Memory Packaging And Interconnect Systems”**

Daniel Cram – Micron Technology

**“Areas Of Conflict And Bottlenecks”**

Joseph J. Riggs - Lucent-Bell Labs - Agere Systems

# FACING THE POWER OF THE FUTURE HIGH END BURN-IN DIRECTIONS AND TRENDS

Marc Knox  
IBM Microelectronics  
Burlington VT

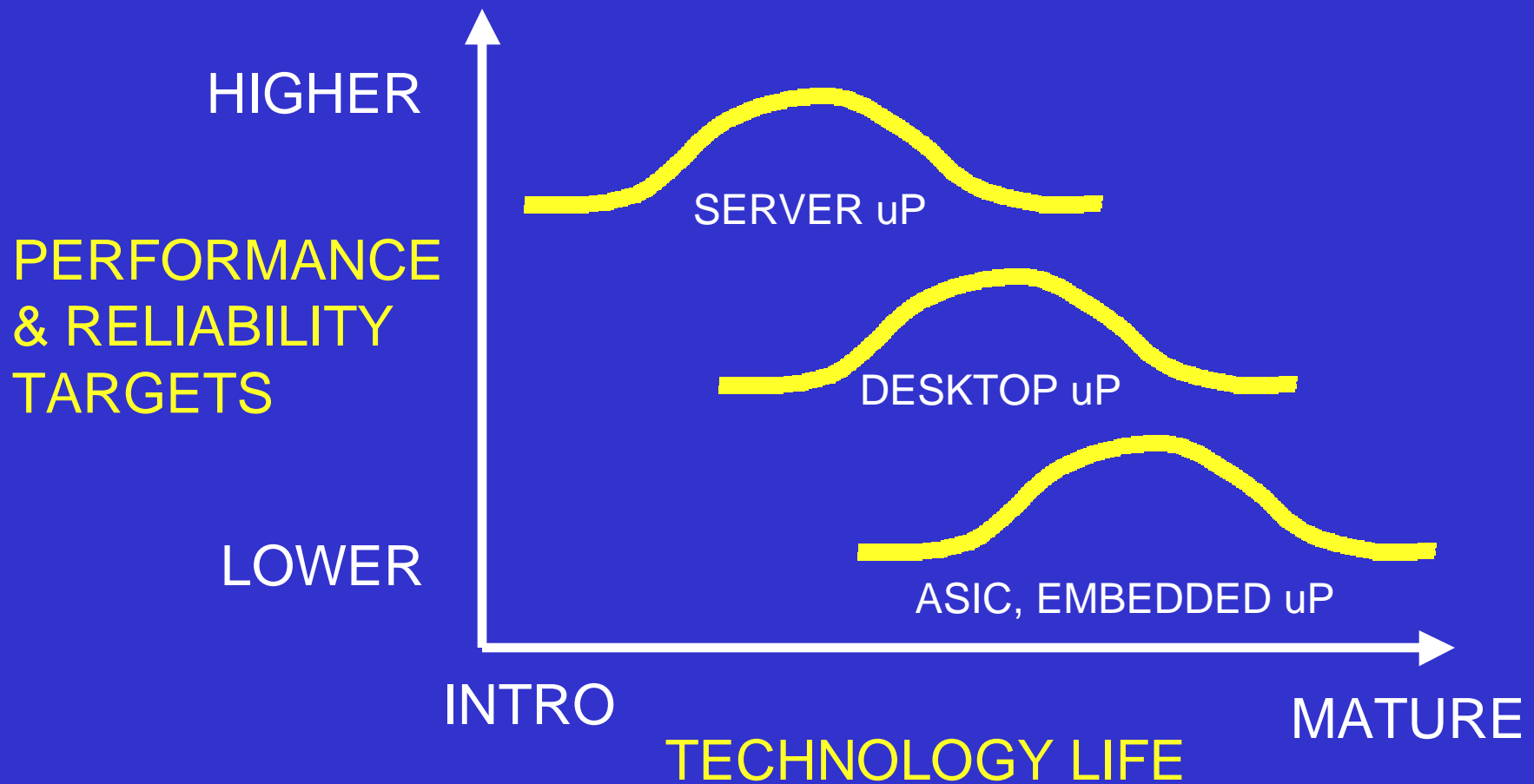
# INTRODUCTION

- High end burn-in is the harbinger of general semiconductor technology trends
- Power at burn-in and test is a first order challenge for high end products today
- Power at burn-in and test will become a challenge across the board in the future
- Innovation, invention and advancement in socket power/thermal performance is critical

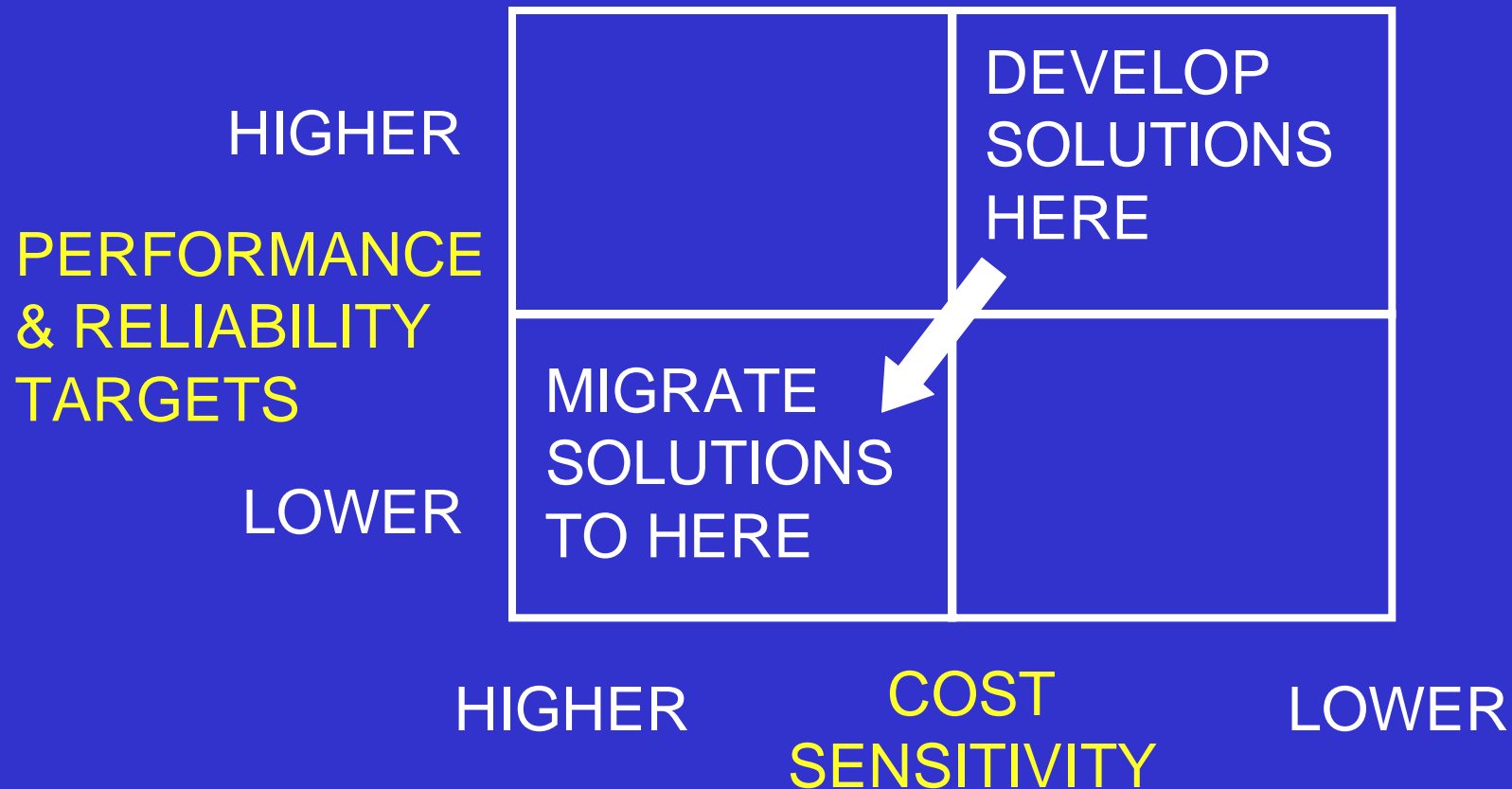
# HIGH END BURN-IN DEFINED

- High transistor count, large die size
- Server and mainframe microprocessors
- Advanced technologies
- High reliability
- High performance
- Ceramic substrate, BGA packages
- Solder ball chip attach

# TECHNOLOGY ROLLOUT (LOGIC)

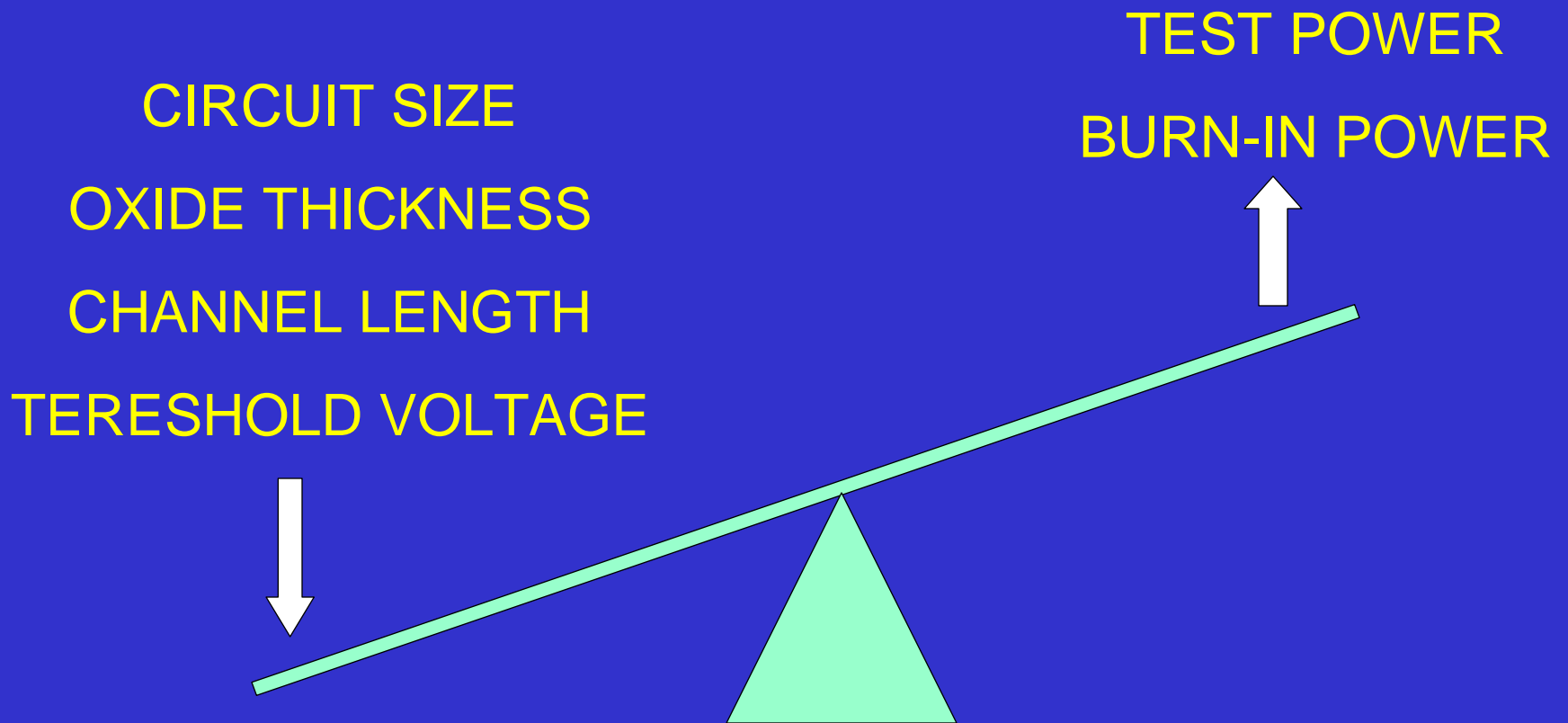


# HIGH END DEVELOPMENT HAS FUTURE LOW END BENEFITS





# PERFORMANCE VS POWER A MARKET DRIVEN CONTEST

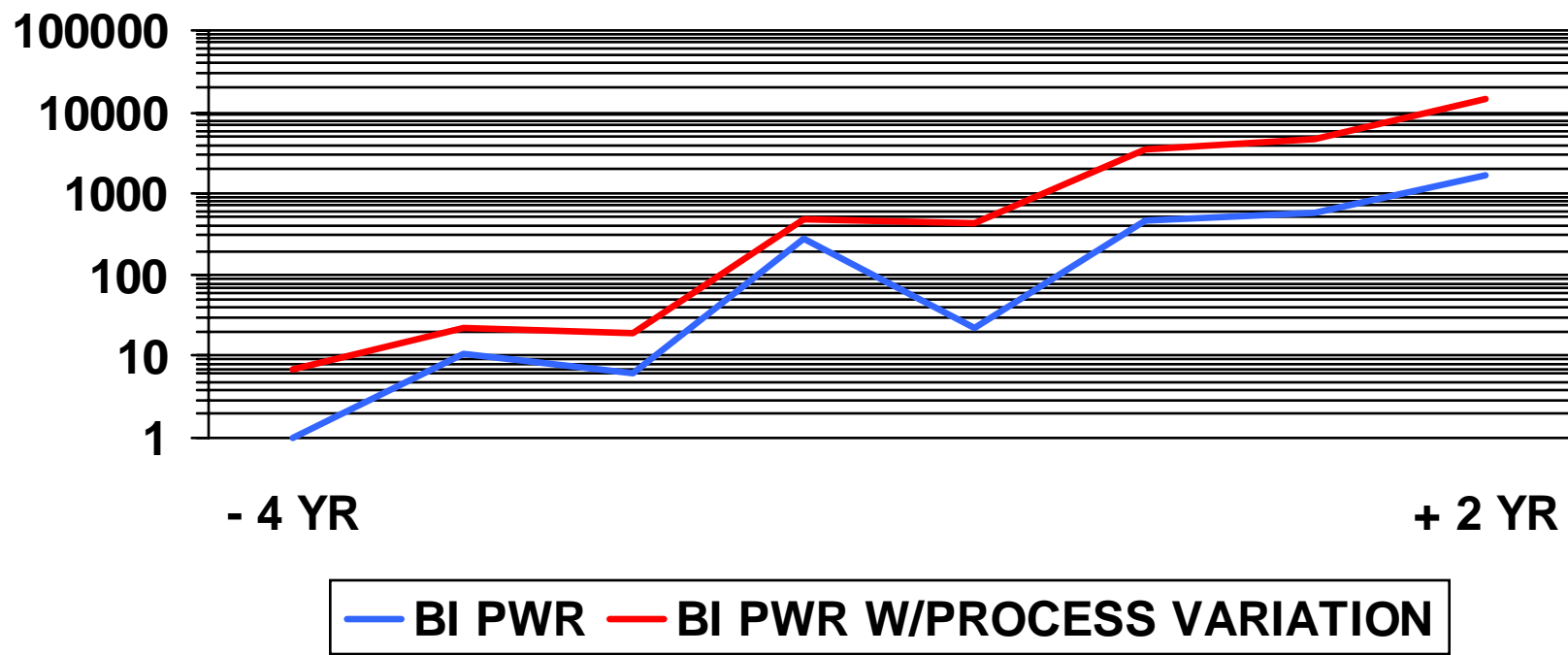


# POWER AT BURN-IN CONDITIONS

- Power is not the same as in the application
- Primary power is DC
- Primary power is sub-threshold leakage ( $I_{off}$ )
- AC power is typically a small portion of BI pwr
- AC power can be modulated by clock speed
- Accelerated temperature of BI increases  $I_{off}$
- Accelerated voltage of BI increases  $I_{off}$

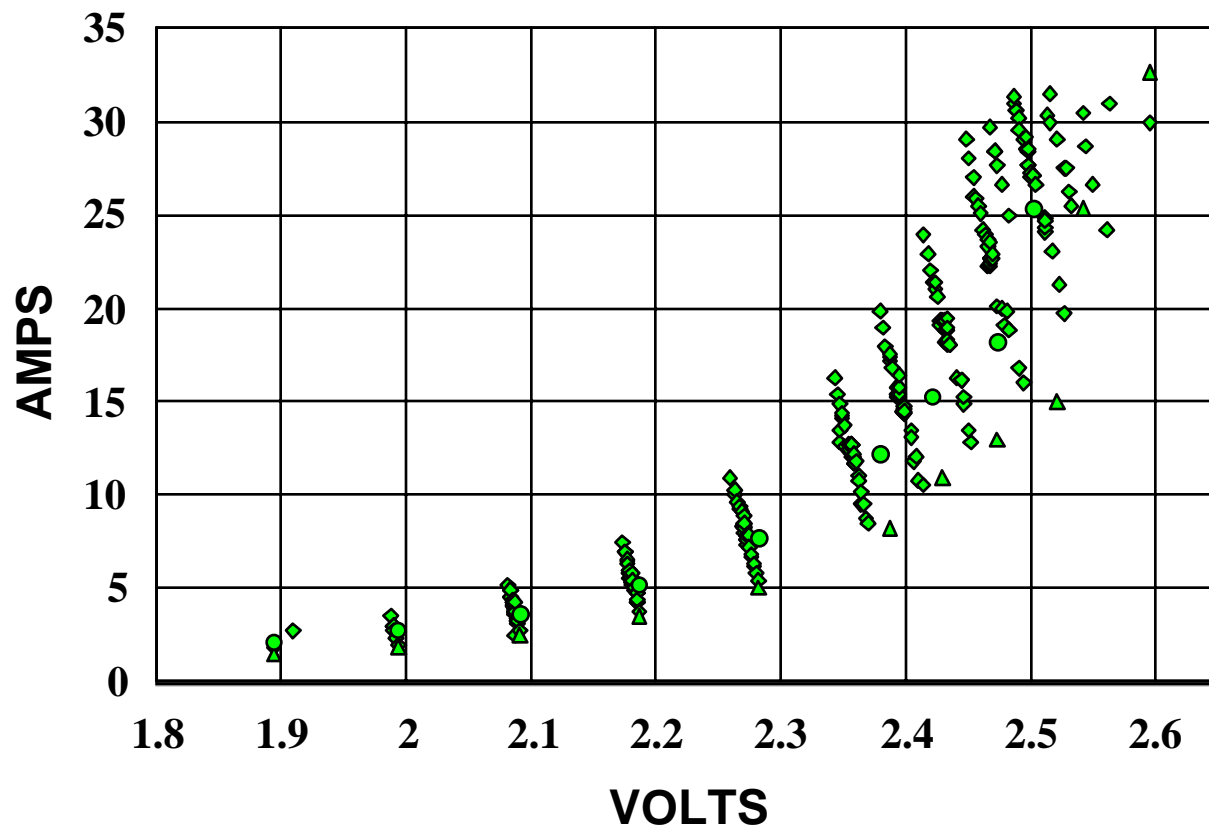
# BURN-IN POWER & TECHNOLOGY PROGRESSION

RELATIVE BI POWER (hold chip size constant)

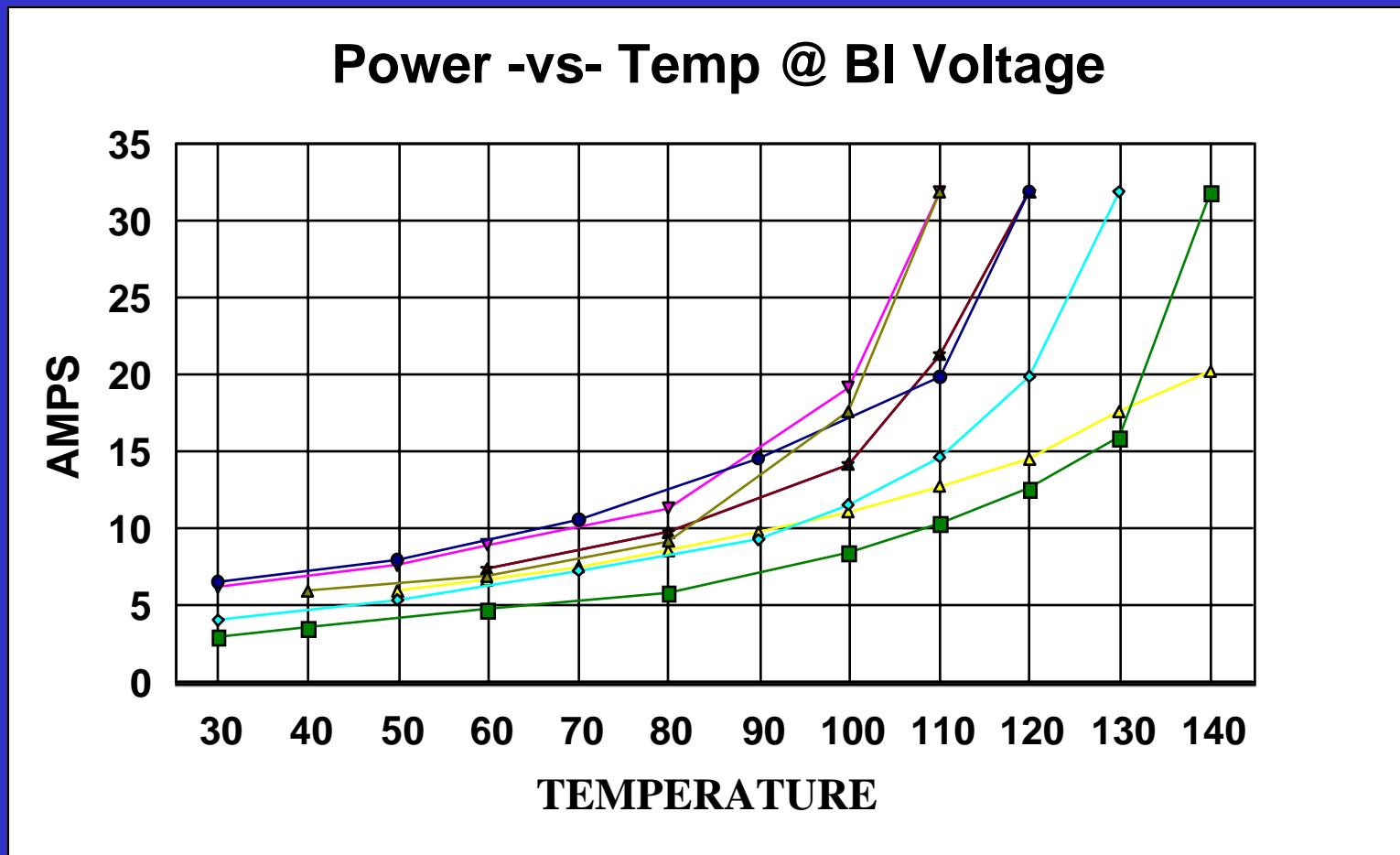


# VOLTAGE VS. POWER A TYPICAL CURVE SET

## Vdd -vs- Current @ BI Temperature



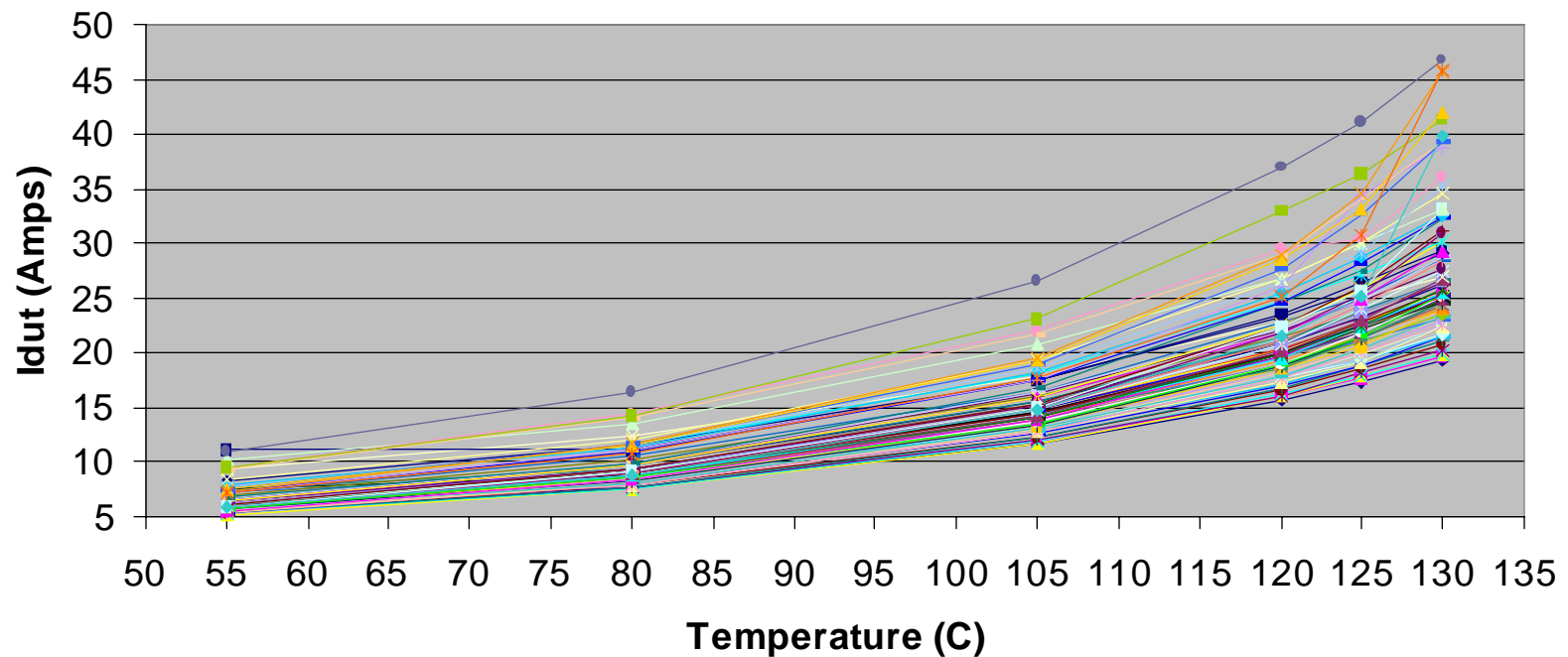
# TEMPERATURE VS. POWER A TYPICAL CURVE SET



# POWER VARIATION

The other half of the first order problem

Typical Distribution Burnin Current vs. Temperature



# DEFINITION OF TERMS

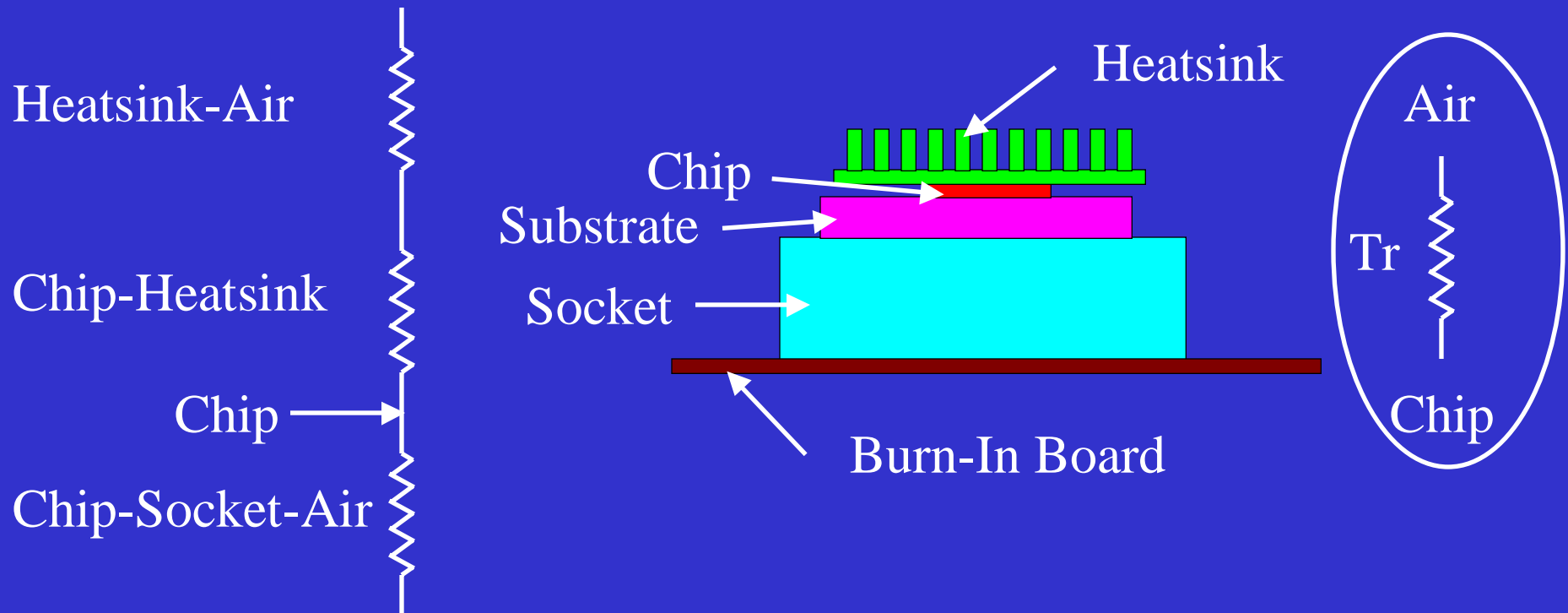
## Power and power variation nomenclature

- Nominal power, +/- variation as % x nom
- 20W, 50% = 10W lowest, 30W highest

## Thermal control nomenclature

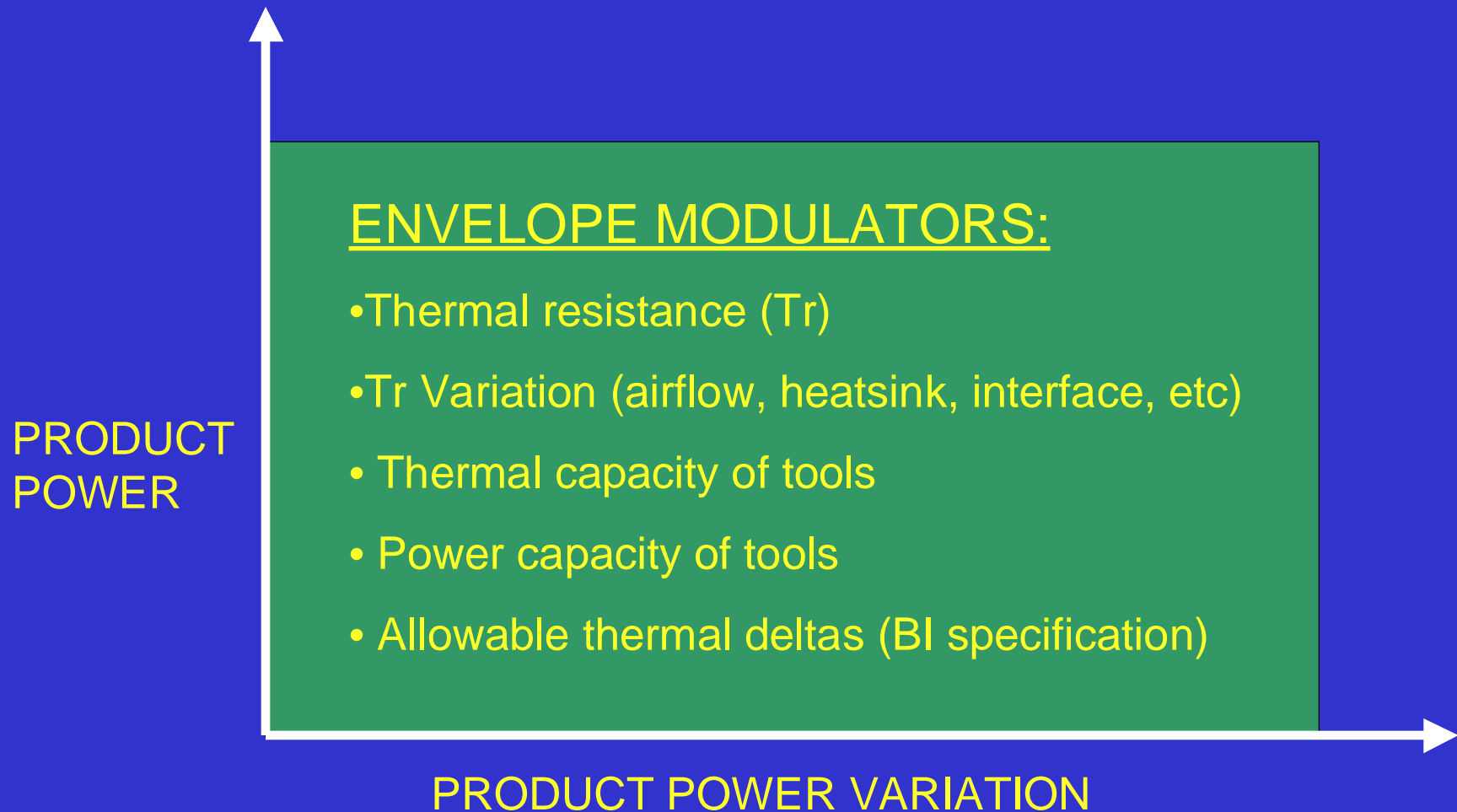
- Passive – no active control, bulk cooling
- Active – control system per DUT
- Active 1 – active heating (or cooling)
- Active 2 – active heating and cooling

# THERMAL RESISTANCE (as used in the examples)

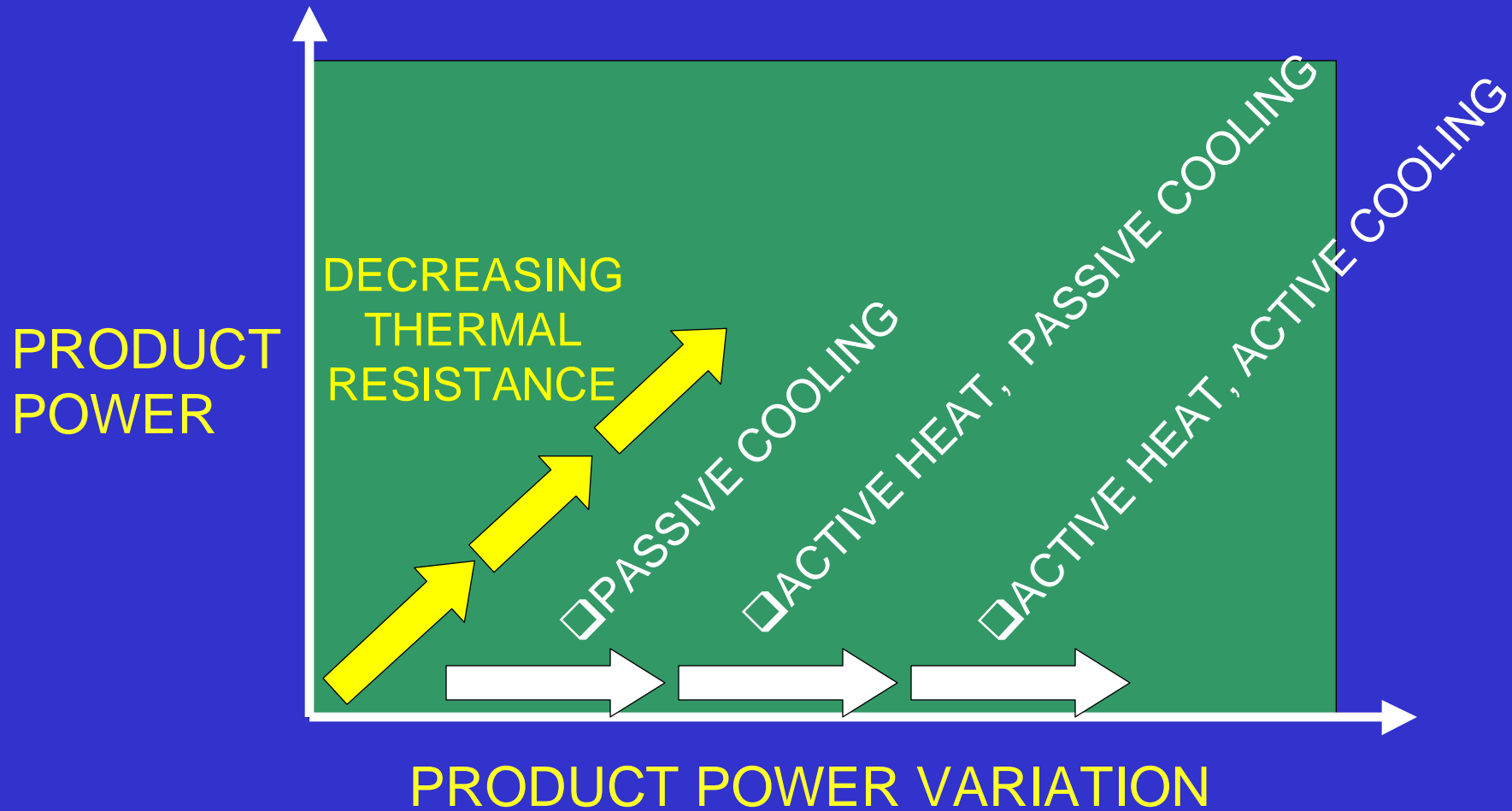




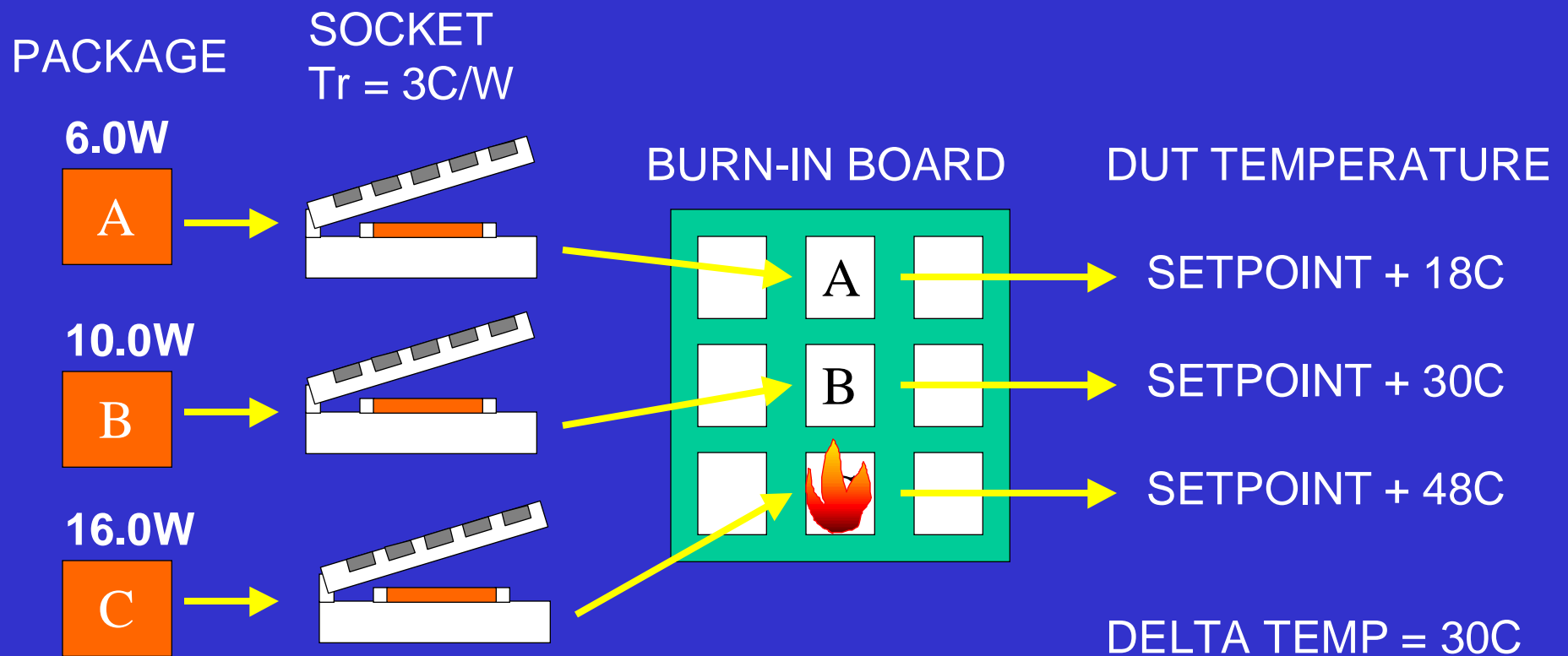
# TOOLING POWER THERMAL CAPABILITY ENVELOPE



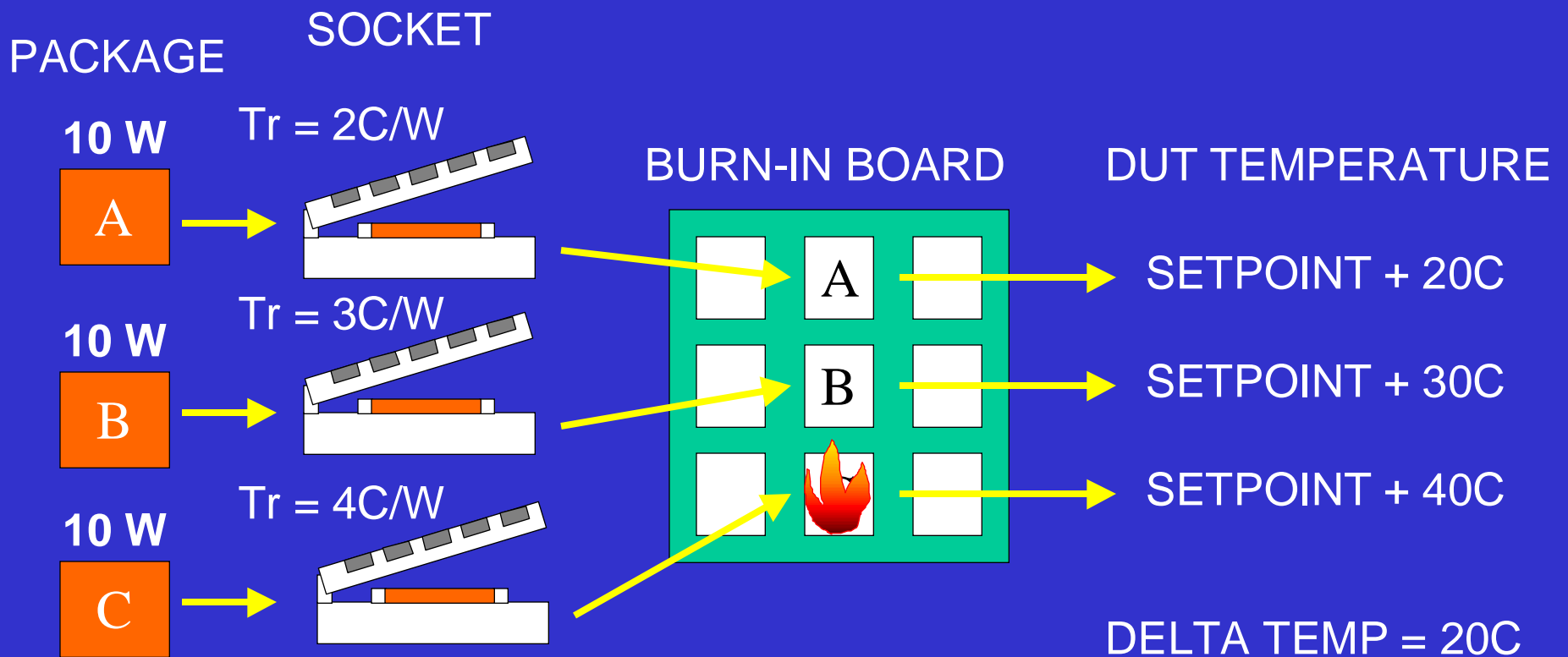
# TOOLING POWER THERMAL CAPABILITY ENVELOPE



# POWER VARIATION IMPACT (passive example)



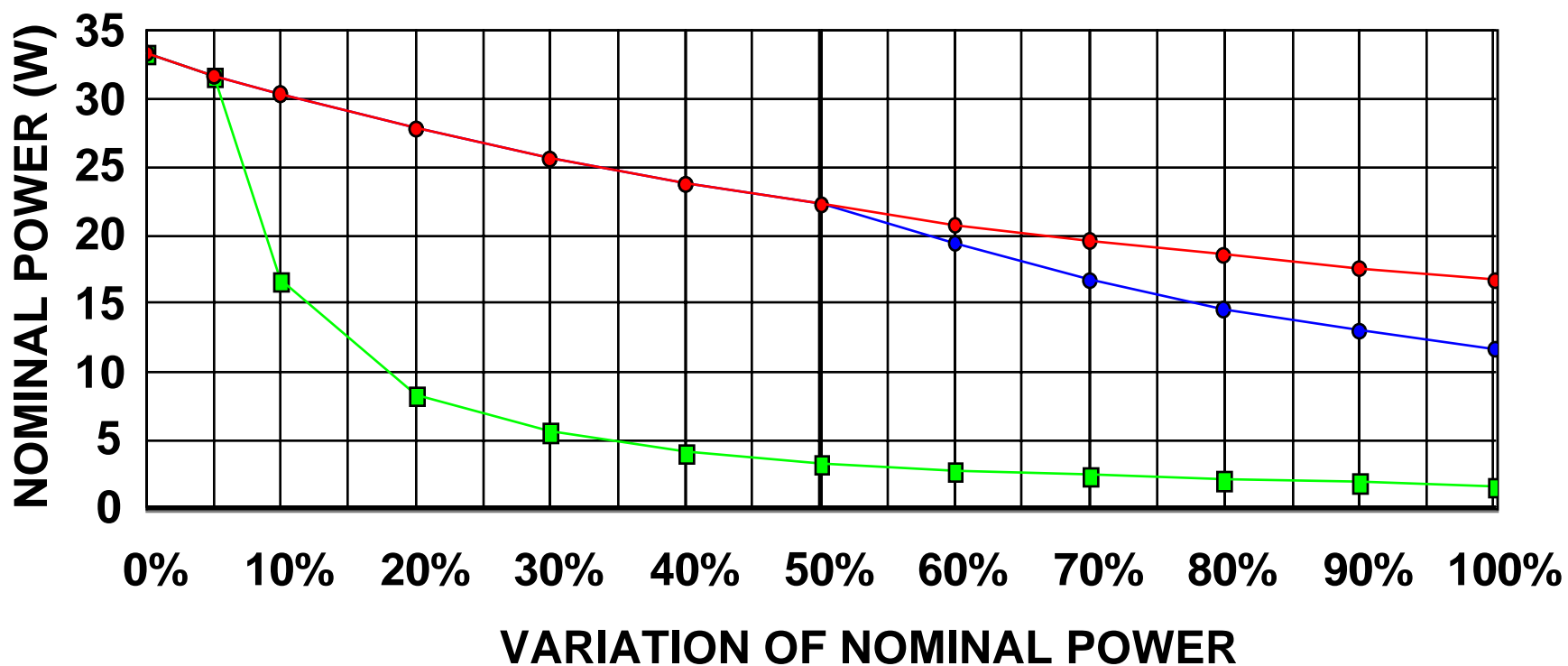
# THERMAL RESISTANCE IMPACT (passive example)



# TOOLING CAPABILITY COMPARISON

3 C/W Socket (no variation), 140C +/-5C DUT Temp Spec

■ PASSIVE ● ACTIVE 1 ● ACTIVE 2

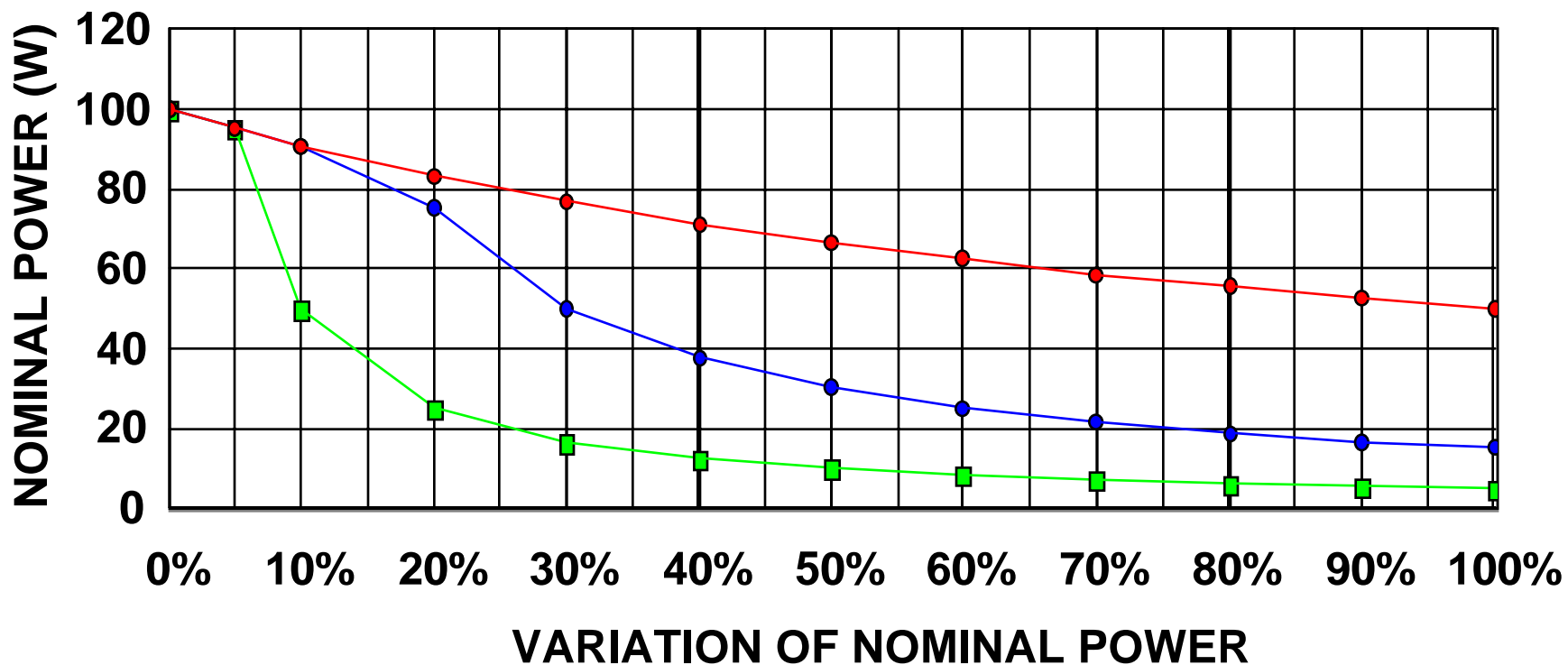


MIN FLUID TEMP = 45C  
20W EFFECTIVE HEATER ON ACTIVE 1

# TOOLING CAPABILITY COMPARISON

1 C/W Socket (no variation), 140C +/-5C DUT Temp Spec

■ PASSIVE ● ACTIVE 1 ● ACTIVE 2

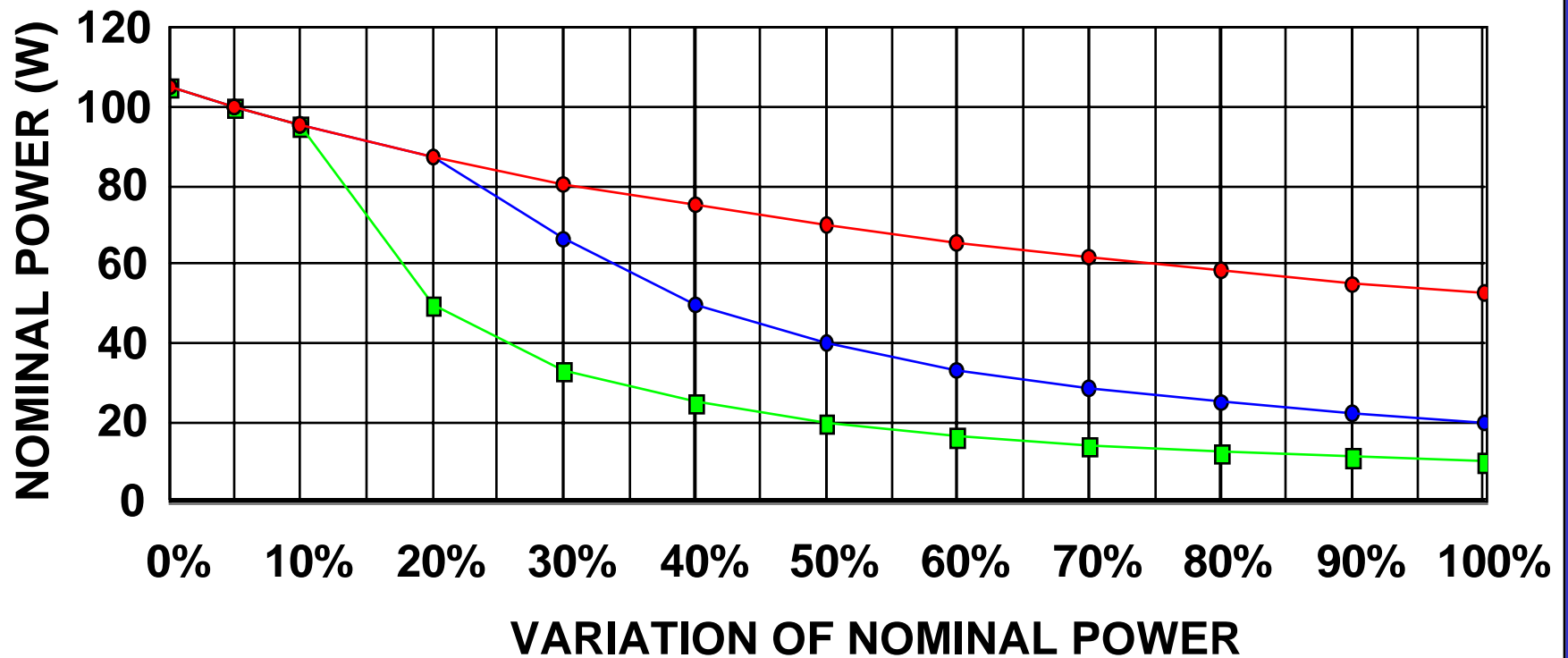


MIN FLUID TEMP = 45C  
20W EFFECTIVE HEATER ON ACTIVE 1

# TOOLING CAPABILITY COMPARISON

1 C/W Socket (no variation), 140C +/-10C DUT Temp Spec

■ PASSIVE ● ACTIVE 1 ● ACTIVE 2



MIN FLUID TEMP = 45C  
20W EFFECTIVE HEATER ON ACTIVE 1

# WHAT ARE THE OPTIONS WHEN TOOLING CAPABILITY IS LIMITED?

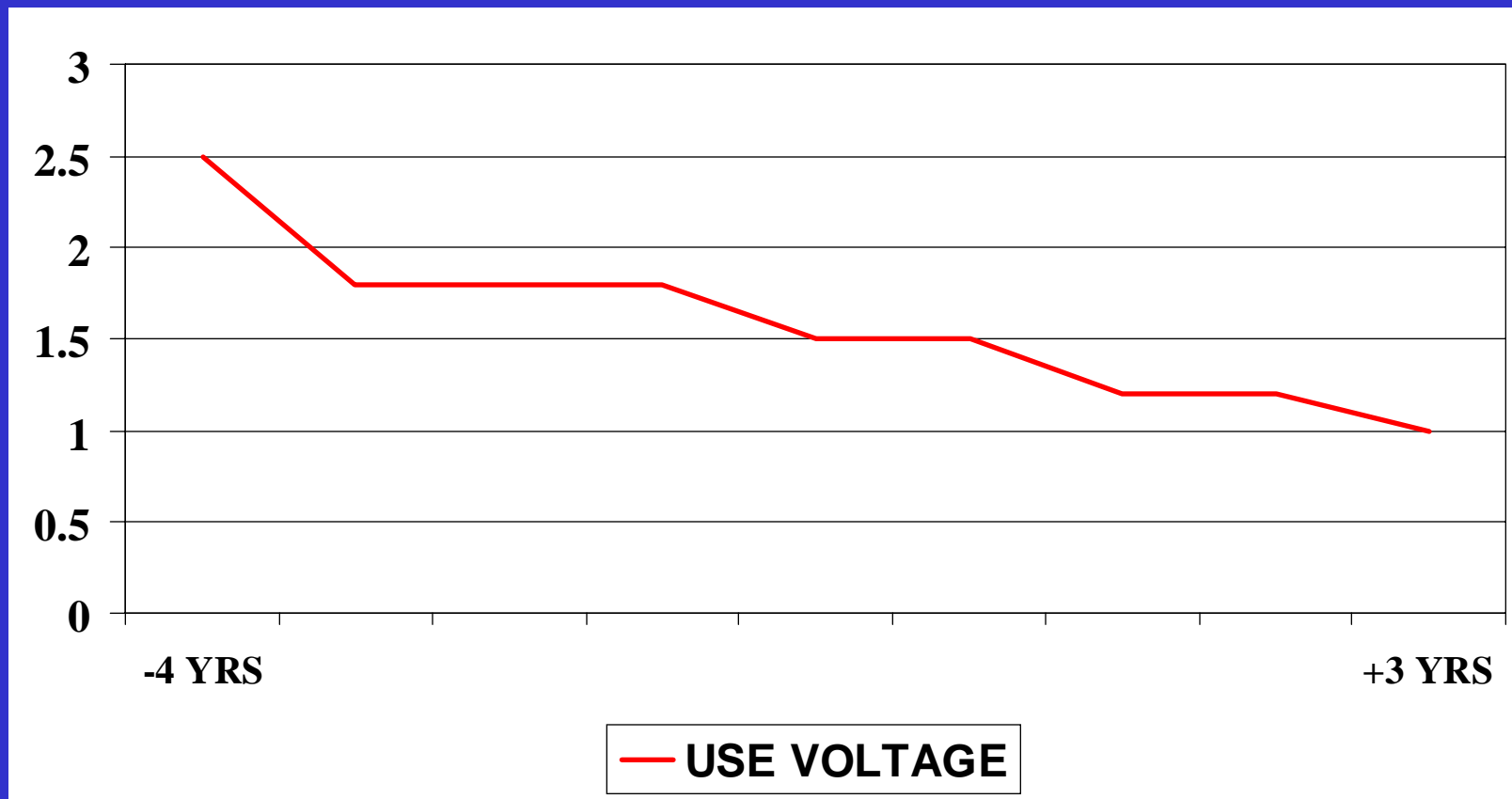
- Reduce the variation of power
  - Sort the distribution
  - Tradeoff is efficiency
  - Understanding tooling capability is critical
- Reduce the power
  - Lower the voltage
  - Lower the temperature
  - Tradeoff is effectiveness of BI (reliability)



# SECOND ORDER TECHNOLOGY TRENDS ALSO IMPACT BURN-IN

- Use voltage decreasing with each technology
  - Voltage delta (use to burn-in) decreases
  - Effective BI acceleration factor decreases
- Power is increasing in the application
  - Leakage ( $I_{off}$ ) and AC (switching)
  - Application temperatures may grow
  - Temp delta (use to burn-in) decreases
- More burn-in required for less reliability

# TECHNOLOGY APPLICATION VOLTAGE TRENDS

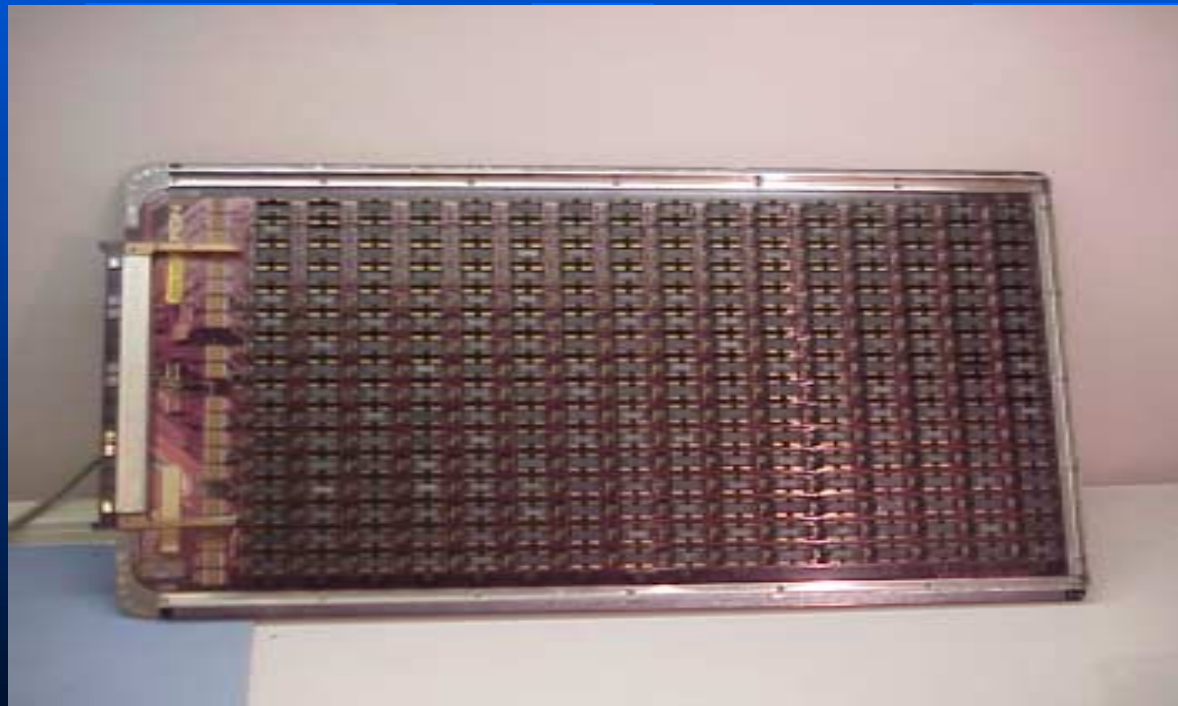


# SOCKET DEVELOPMENT KEY FOCUS AREAS, A SHORT LIST

- Thermal solutions, thermal solutions, thermal solutions
- Low resistance thermal solutions
  - Chip interface, heatsinks, socket body
- Heat/cool thermal solutions
- Compliant thermal interface
- Robust temperature sensors
- Cost effective thermal solutions

# BURNIN OF MEMORY DEVICES

A look at the past, present and future of memory packaging and interconnect systems.



Daniel Cram



# AGENDA

## ■ DRAM

- What is it?
- What is BurnIn?

## ■ MEMORY PACKAGING

- Driving forces

## ■ BURNIN SOCKET TYPES

- Clamshell
- LIF
- ZIF

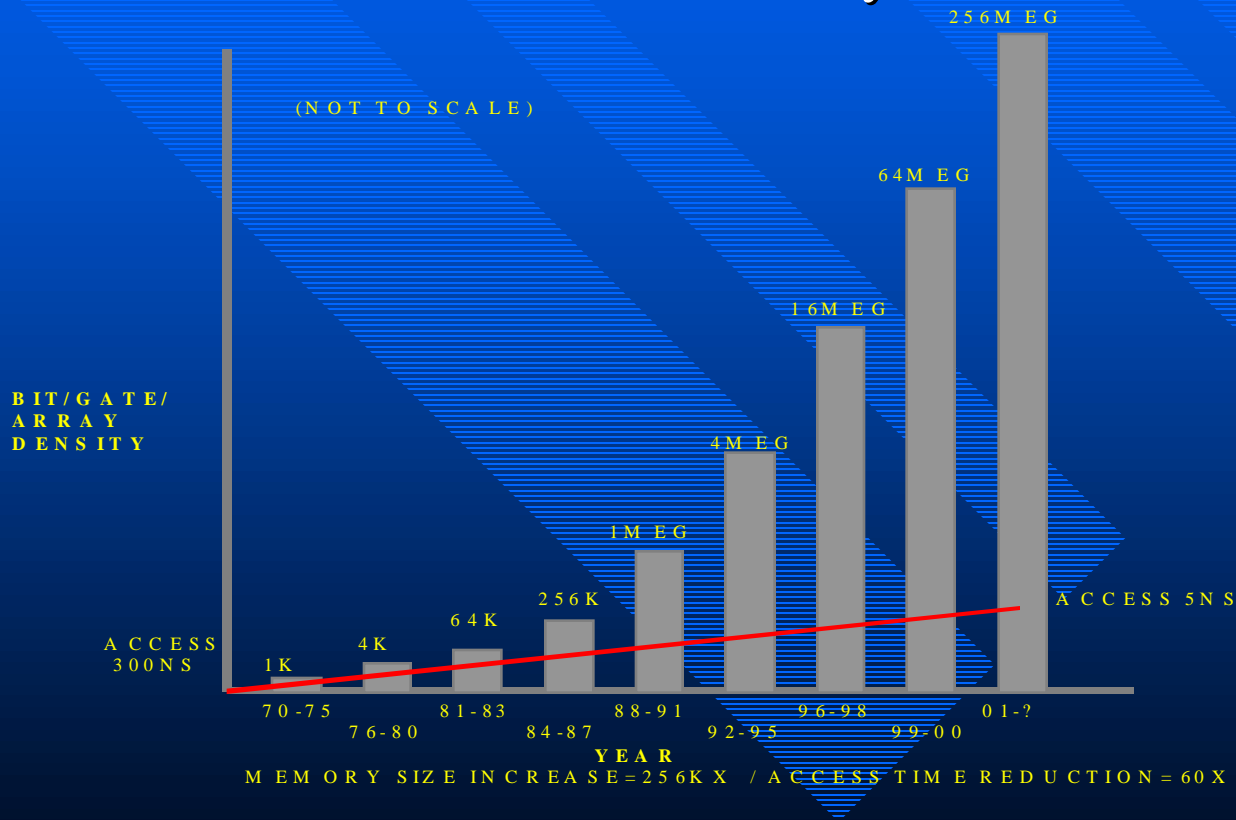
## ■ SOCKET COST

- Packaging cost

## ■ FUTURE?

# DRAM

- Dynamic Random Access Memory
- Background
- DRAMs are a commodity/Refresh



# BURNIN

## ■ MONITORED/INTELLIGENT

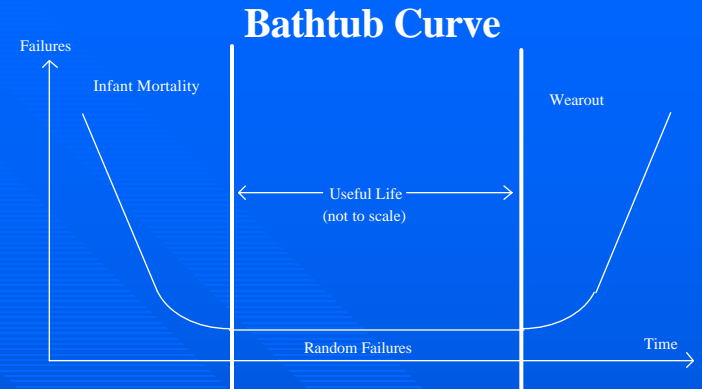
- FAILURES IN TIME
- REDUCED BURN RATES/RAPID DURATION REDUCTION
- GANGED TEMPERATURE ENVIRONMENT

## ■ MPT

- BATCH PROCESS
- DATA RETENTION/TIME INTENSIVE TESTS

## ■ SPEED MATTERS

- TEST SYSTEM IS INTERCONNECT SENSITIVE
- INTEGRATED WAVEFORMS
- NANO SECOND EVENTS/OVER-KILL/FALSE FAILURES



# MEMORY PACKAGING

## ■ HISTORY

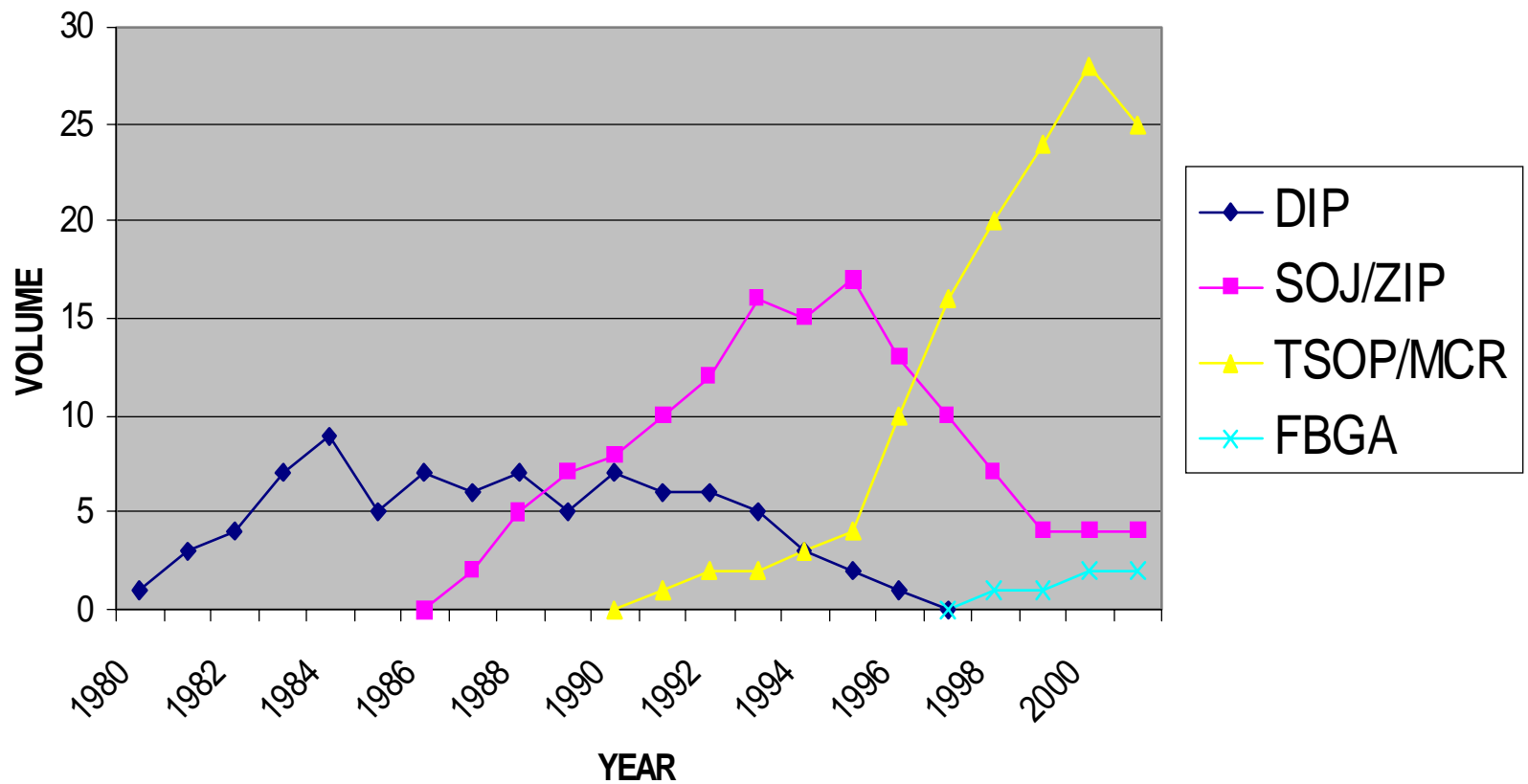
- Memory packaging, over the last 20 years, can be divided into four primary groups; DIP, SOJ, TSOP, & FBGA.

## ■ PITCH PROGRESSION/LEAD COUNT

- DIP 2.54MM  $\leq$  18 LEAD
- SOJ 1.27MM/.8MM  $\leq$  42 LEAD
- TSOP .8MM/.65MM/.5MM  $\leq$  86 LEAD
- FBGA .8MM/.75MM  $\leq$  90 BALL

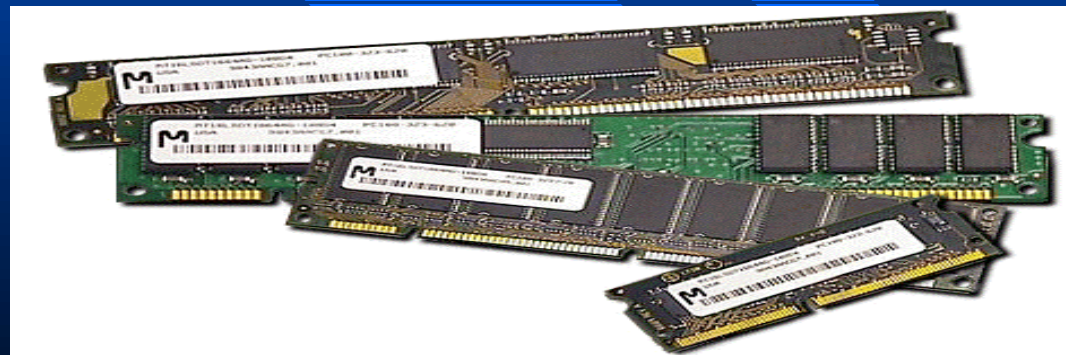


# MEMORY PACKAGING



# DRIVING FORCES FOR PACKAGE CHANGE

- I/O COUNT - Wider buss - Increased array size
- Mother board space/module density (Surface mount)
- Die size
- Package electrical performance
- Memory modules have become one of the primary driving forces for component size and outline



# BURNIN SOCKET TYPES

- Three basic types
  - Clamshell
  - LIF (Low Insertion Force)
  - ZIF (Zero Insertion Force)
  
- Package typically dictates designed required, however, other driving factors are;
  - Level of automation needed
  - Environment
  - Pitch
  - Level of performance
  - Cost
  - etc.

# CLAMSHELL

## ■ Advantages

- Reliable interconnect
- Standardized contact/body outline
- Can accommodate quad and large pin arrays

## ■ Disadvantages

- High part count
- Two additional steps for automation
- High cost

## ■ PRIMARY ROLE

- For TSOP/QFP early development

# LIF

## ■ Advantages

- Large surface area/scrub zone
- Low part count
- Ease of automation
- Low cost

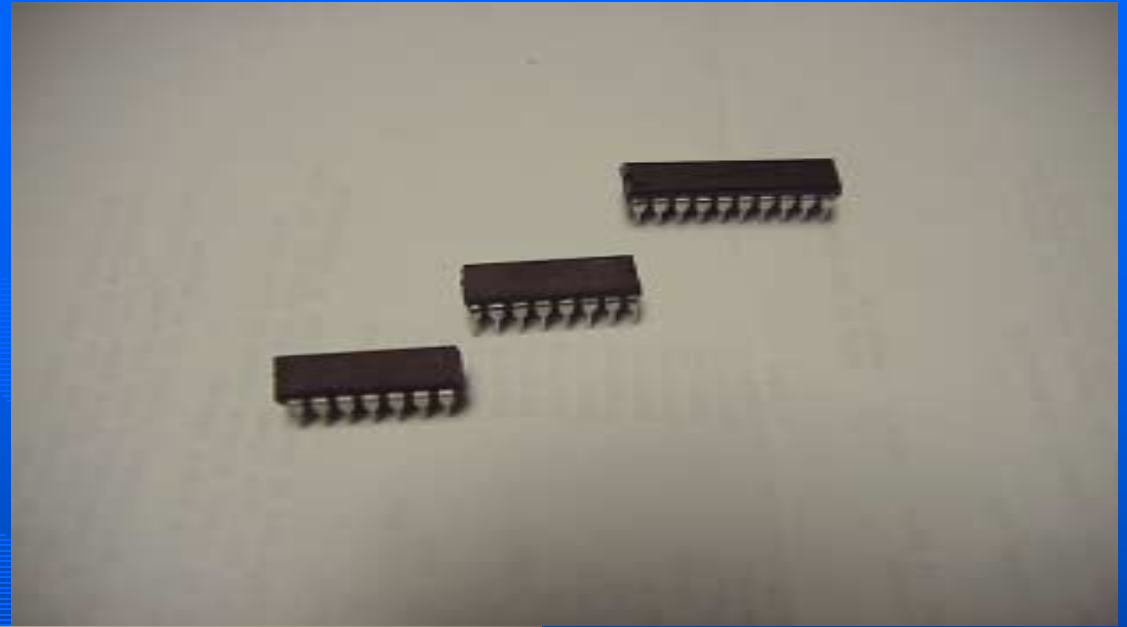
## ■ Disadvantages

- Practical pitch limitation is .8mm
- <50LD I/O count
- Package/lead-frame damage due to direct entry

## ■ PRIMARY ROLE

- For DIP, SOJ, & MCR

# DIP

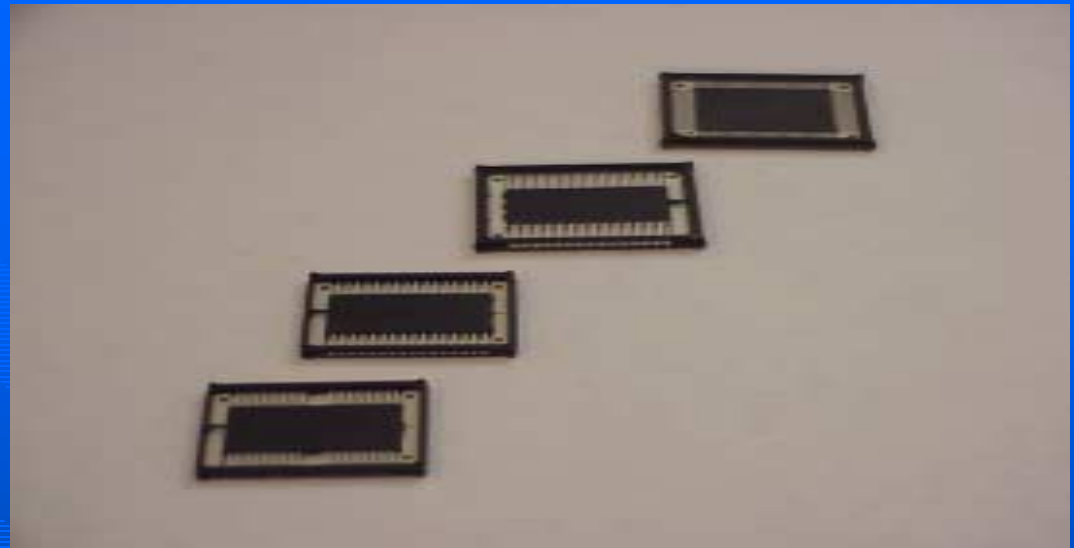


Daniel Cram  
Micron Technology

# SOJ



# MCR



Daniel Cram  
Micron Technology



# ZIF

## ■ Advantages

- Accommodates tight pitch with limited lead damage
- Lower component count than clamshell
- Pitches down to .5mm
- Ease of automation
- Low cost

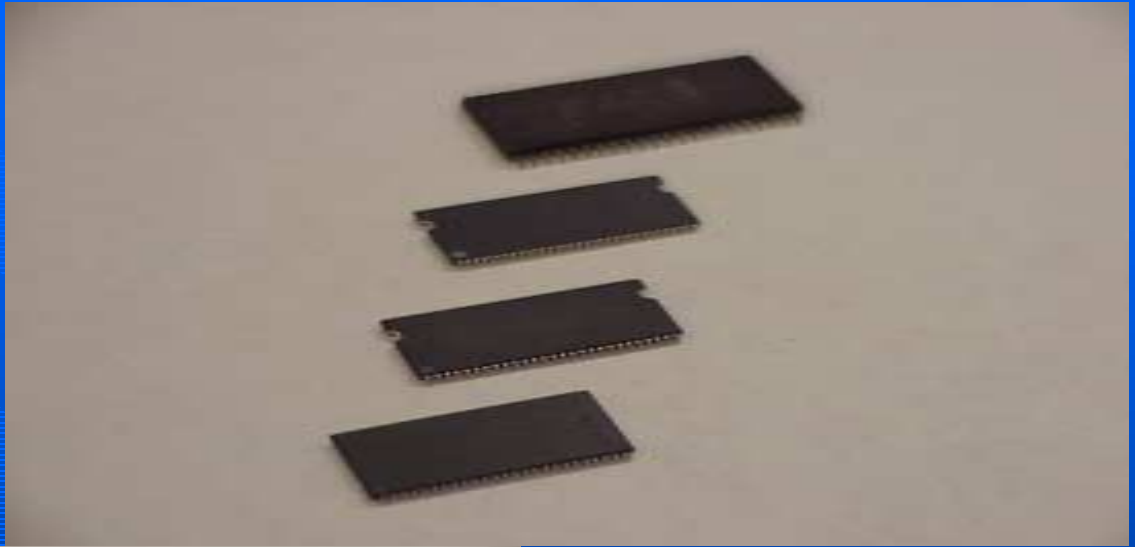
## ■ Disadvantages

- Limited scrub area or wipe zone
- Prone to long-term tin/lead transfer failure

## ■ PRIMARY ROLE

- For TSOP

# TSOP



Daniel Cram  
Micron Technology

# ZIF FBGA

## ■ Advantages

- Accommodates tight pitch with limited ball damage
- Pitches down to .65mm
- Ease of automation
- Multi-point contact designs

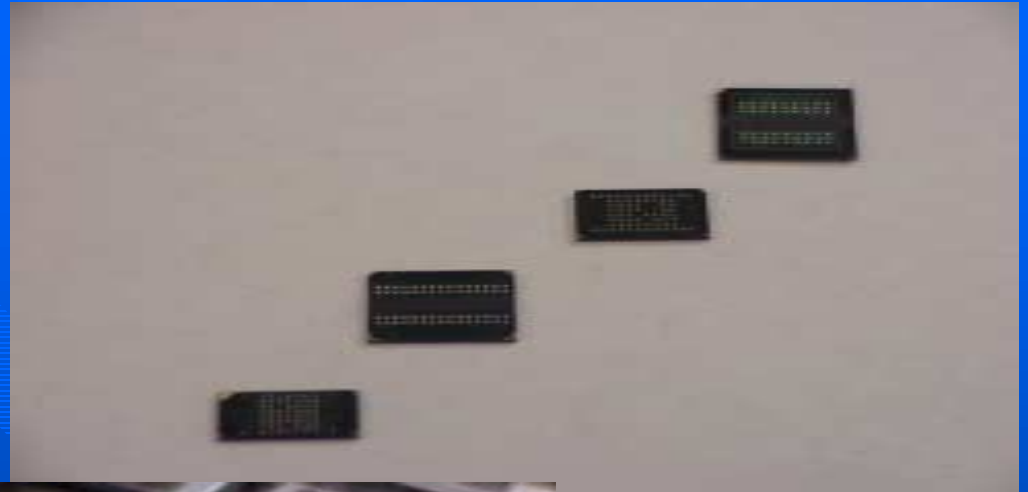
## ■ Disadvantages

- Lack of standard/long lead-time for new array
- Prone to tin/lead build up and reflow (Ball damage/sticking/etc.)
- High cost

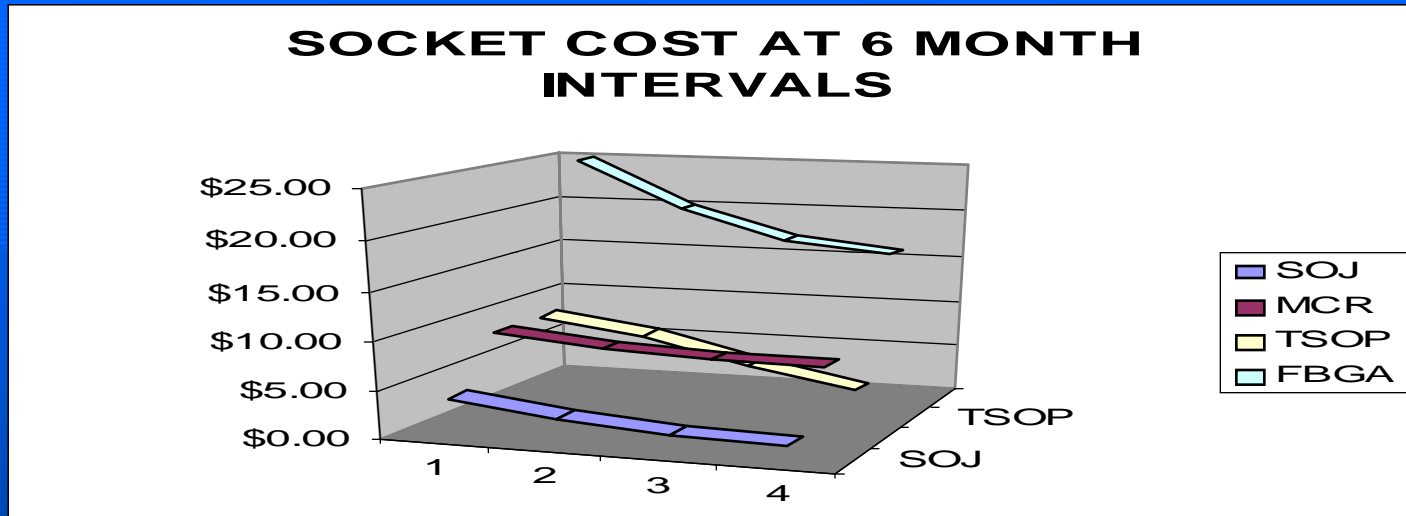
## ■ PRIMARY ROLE

- For FBGA

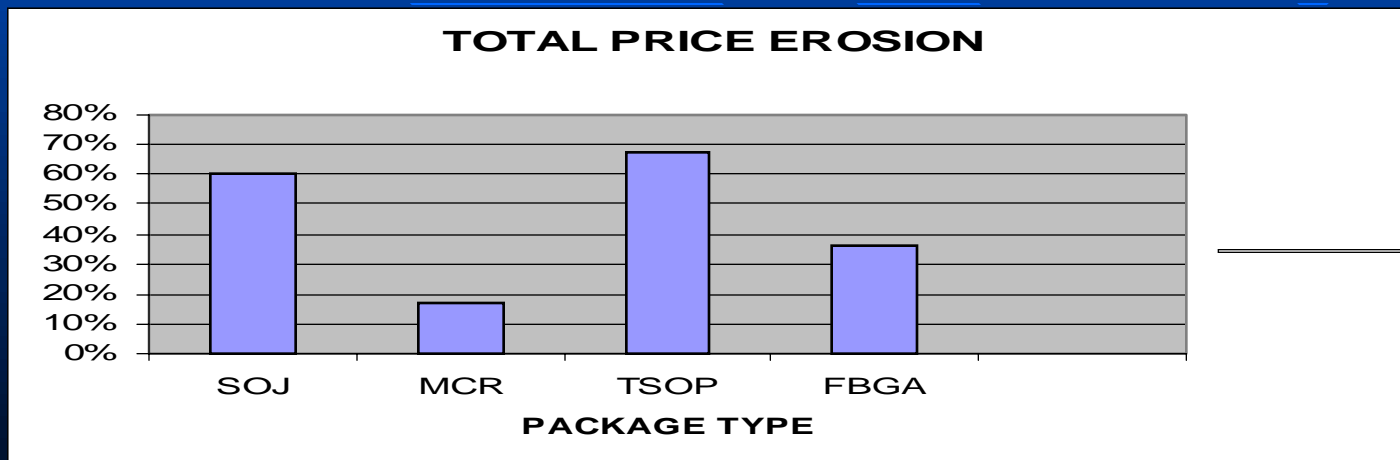
# FBGA



# SOCKET COST

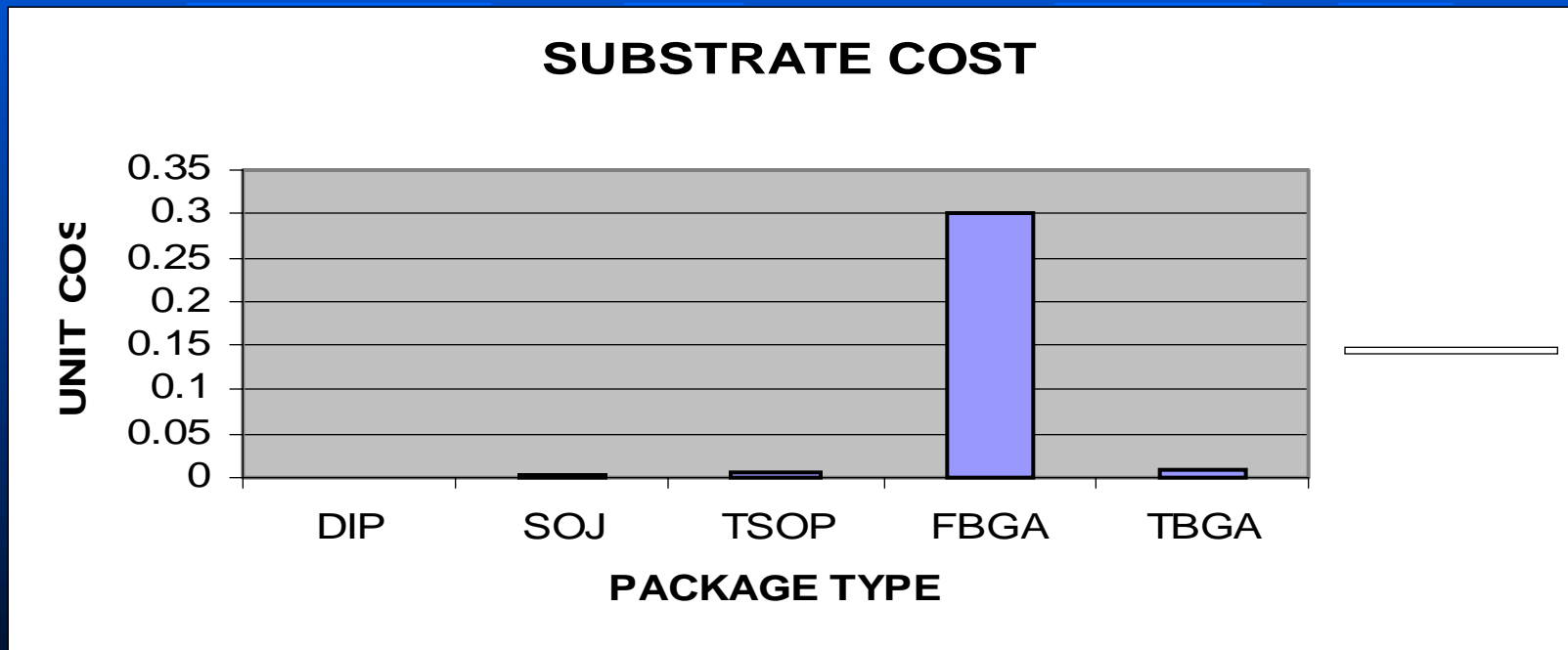


(What do sockets really cost to make anyway?)



# PACKAGE COST

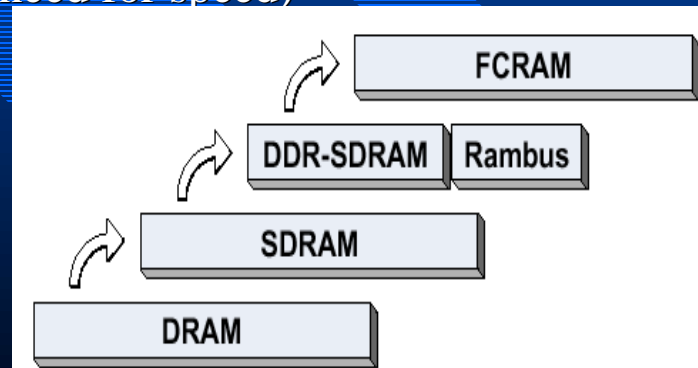
- The primary cost in the packaging has always been the lead-frame or substrate.



# FUTURE?

- **Finer pitch FBGA/CSP packages**
  - <=.5mm
  - COB, FCIP, etc.
- **Flip-Chip**
- **Memory based MLF package?**
- **Due to high cost of test fixturing**
  - Test in strip
  - Module level
  - Wafer level

(The need for speed)



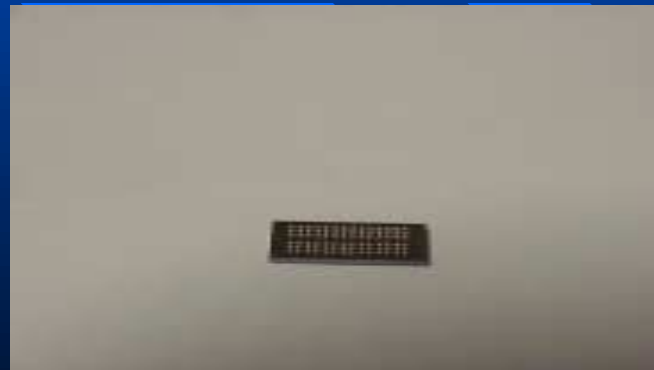
# FBGA/CSP

- Even if the cost of the package drops the cost of the sockets remain high.
- Solder transfer and reflow problems remain a stigma
- Package/substrate integrity?
- TBGA
  - Tape based ball grid array appears to be a cheap alternative to rigid and semi-rigid substrates.



# FLIP-CHIP

- Redistribution technology is still maturing.
- Pad array/grid is outline dependant
  - Die shrink can force retooling
- Handling bare die
  - Chipping/cracking
- If bumped
  - requires clamshell or force distribution method



# STRIP TESTING

- Adjacent cell electrical connections must be isolated
- Socket/board density can be negatively impacted
- Matrix lead-frame generally do not accommodate this approach
- Failures tie-up process unless excised
- Second pass excise operation
- Etc.,Etc...



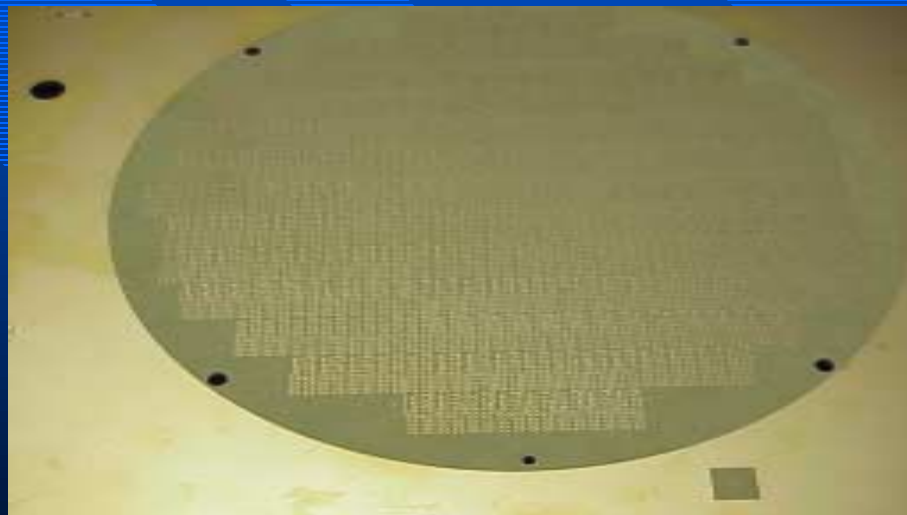
# MODULE LEVEL

- Solder joint damage/cracks
- Passive component damage
- Module repair bottleneck
- Ultimate cost of scrap and recovery efforts
- Module size and power requirements could be issue for typical chambers
- Conventional/singulated component sockets may still have to be developed



# WAFER LEVEL

- Die shrink requires retooling
- High risk associated with wafer handling/processing (ie: Scrap cost \$\$)
- Conventional socketing/tooling would still have to be developed



# SUMMARY

- The single greatest challenge facing the memory producers is cost. (Margins are tight.)
- The demand for KGD is greater now than it ever was. (But the cost to process remains high.)
- The ultimate direction will likely be a variant of all the noted possibilities with production and cost factors dictating
- MODULE density, cost and performance being a primary goal/driving force

# *AREAS OF CONFLICT AND BOTTLENECKS*



Joseph J. Riggs  
Lucent-Bell Labs  
Agere Systems  
Allentown, Pennsylvania

# *Abuser of Test and Burn-In Sockets*



- 1. Used at high and low temperatures
- 2. Thousands of BI cycles
- 3. Expect the sockets to work on all pins at test conditions

# *BI & Reliability at the Back End*

- 1. Must worry about the small stuff or the job can become messy
- 2. Examples:
  - A. Titanic - 1912
  - B. Mars Lander - 1999
  - C. Company XYZ designing and packaging a device where a test and BI socket did not exist - 1995



## *Small Stuff*



- 1. Chip & Package Designers
  - A. Not aware of testing and BI
  - B. Not familiar with Reliability
  - C. Do not think about job cost

## *Small Stuff*



- 2. Cost
- A. \$0.50 to \$1.00 per pin
- B. \$3,000-\$10,000 socket cost per BI board
- C. Designers and Socket Manufactures share the blame

## *Small Stuff*



- 3. Reliable
- A. All pins work at test and BI conditions
- B. 100k or more device cycles required
- C. 1k or more BI cycles required
- D. Socket repair and replacement easy

## *Small Stuff*



- 4. Temperature
- A. Clam shell Vs. open top
- B. Open top Vs. no top
- C. No data available

## *Small Stuff*



- 5. Drawings
  - A. On time and accurate
  - B. Able to read (Customer's Language)
  - C. Metric & English measurements
  - D. Drawings reflect the socket
  - E. Samples available

## *Small Stuff*



- 6. Standard Footprints
- A. Standard footprints for device family
- B. Standard socket pin spacing
- C. Check with PCB manufactures

## *Small Stuff*



- 7. Electrical Characteristics
  - A. Low contact resistance, inductance and capacitance
  - B. Maintain low values through lifetime

## *Small Stuff*



- 8. Auto Load/Unload
- A. Desired?
- B. Difficult
- C. “Not my problem!”



## *Small Stuff*



- 9. Socket data
- A. Difficult to obtain
- B. Inaccurate
- C. User asked to evaluate socket
- D. Data sometimes obtained from peers

## *Small Stuff*



- 10. Cooperation
- A. Work together
- B. Share data
- C. Evaluate problems together
- D. Solve together

## *Conclusions*



- 1. Small stuff can be killers
- 2. Without cooperation at all levels, the back end of the job can be messy

# *Questions?*



- Contact:
- Mr. Joseph J. Riggs
- Lucent-Bell Labs
- Agere Systems
- 555 Union Blvd.
- Allentown, PA 18109
- 610-712-6433
- [jjriggs@lucent.com](mailto:jjriggs@lucent.com)